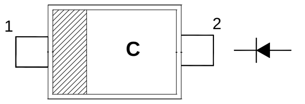
RB521S-30

SILICON EPITAXIAL PLANAR SCHOTTKY BARRIER DIODE

for low current rectification and high speed switching applications

PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode



Top View
Marking Code: "**C**"
Simplified outline SOD-523 and symbol

Features

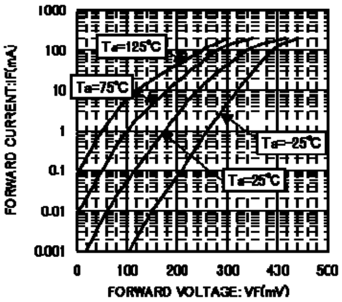
- Extremely small surface mounting type

Absolute Maximum Ratings (T_a = 25 °C)

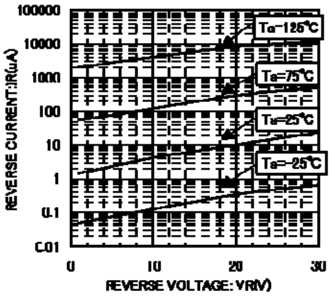
Parameter	Symbol	Value	Unit
Reverse Voltage	V_R	30	V
Mean Rectifying Current	I_O	200	mA
Peak Forward Surge Current (60Hz for Cyc.)	I_{FSM}	1	A
Junction Temperature	T_j	125	°C
Storage Temperature Range	T_{stg}	- 40 to + 125	°C

Characteristics at T_a = 25 °C

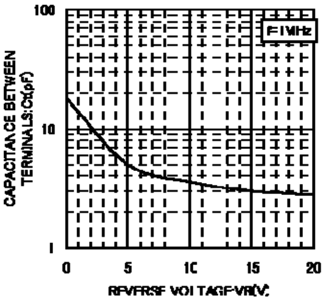
Parameter	Symbol	Max.	Unit
Forward Voltage at I_F = 200 mA	V_F	0.5	V
Reverse Current at V_R = 10 V	I_R	30	µA



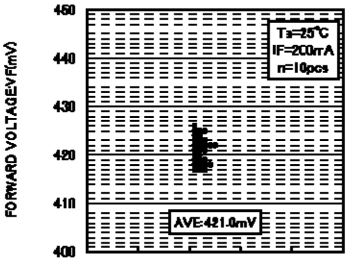
VF-IF CHARACTERISTICS



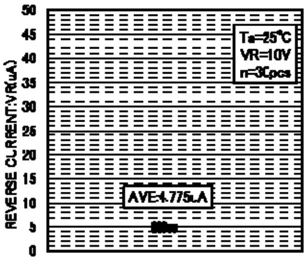
VR-IR CHARACTERISTICS



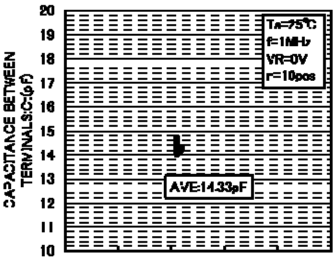
VR-Ct CHARACTERISTICS



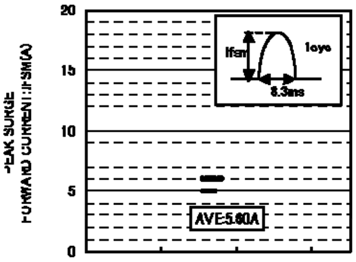
VF DISPERSION MAP



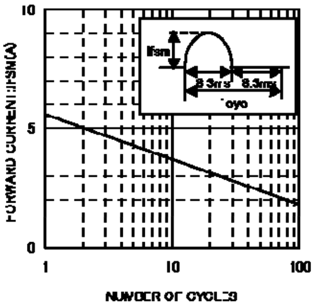
IR DISPERSION MAP



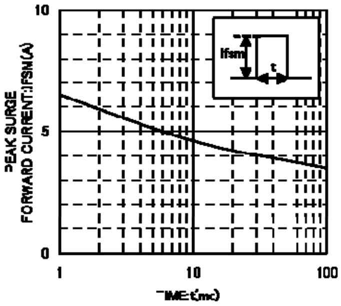
Ct DISPERSION MAP



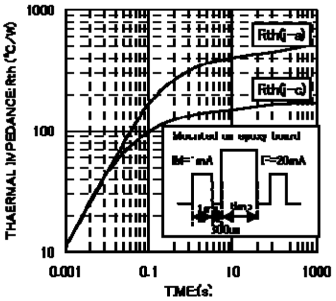
IFSM DISPERSION MAP



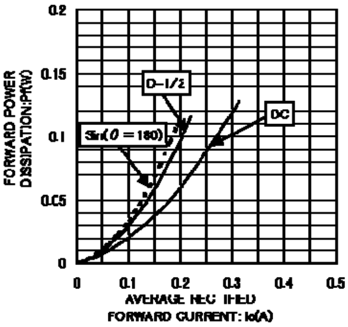
IFSM-CYCLE CHARACTERISTICS



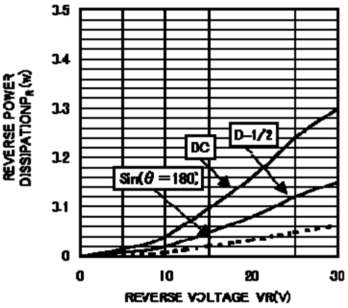
IFSM-t CHARACTERISTICS



Rth-t CHARACTERISTICS



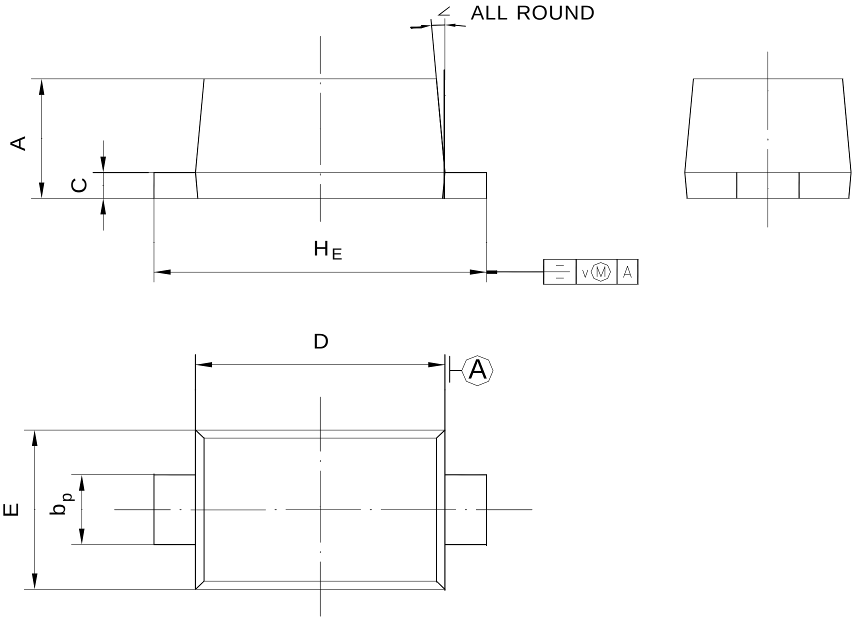
Io-Pf CHARACTERISTICS



VR-P_R CHARACTERISTICS

PACKAGE OUTLINE

Plastic surface mounted package; 2 leads **SOD-523**



UNIT	A	b_p	C	D	E	H_E	V	∠
mm	0.70 0.60	0.4 0.3	0.135 0.100	1.25 1.15	0.85 0.75	1.7 1.5	0.1	5°